

ECE 511 - Lecture 28

Note Title

5/9/2013

$$V_{ref} = \alpha_1 \underbrace{V_{BE}}_{CTAT} + \alpha_2 \underbrace{\left(V_T \ln k \right)}_{PTAT} \quad \checkmark$$

$\frac{kT}{q}$

We want $\frac{\partial V_{ref}}{\partial T} = 0$

$$\alpha_1 \cdot \frac{\partial V_{BE}}{\partial T} + \alpha_2 \left(\frac{k}{T} \ln k \right) = 0$$

$$\Rightarrow \alpha_2 \ln(k) = - \frac{\alpha_1 \cdot \frac{\partial V_{BE}}{\partial T}}{k/q} = 17.2 \alpha_1$$

$-1.5 \text{ mV}/^\circ\text{K}$

$0.087 \frac{\text{mV}}{^\circ\text{K}}$

choose $\alpha_1 = 1$

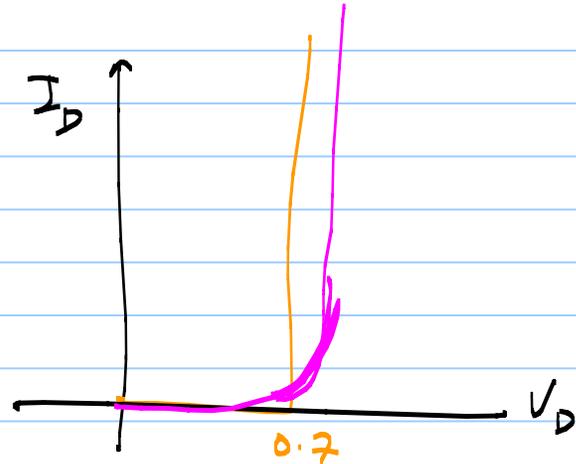
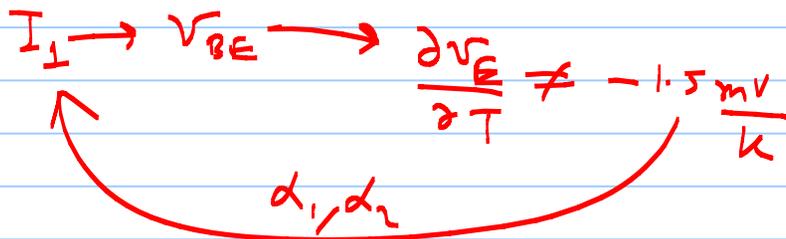
$$\alpha_2 h_k = 17.2$$

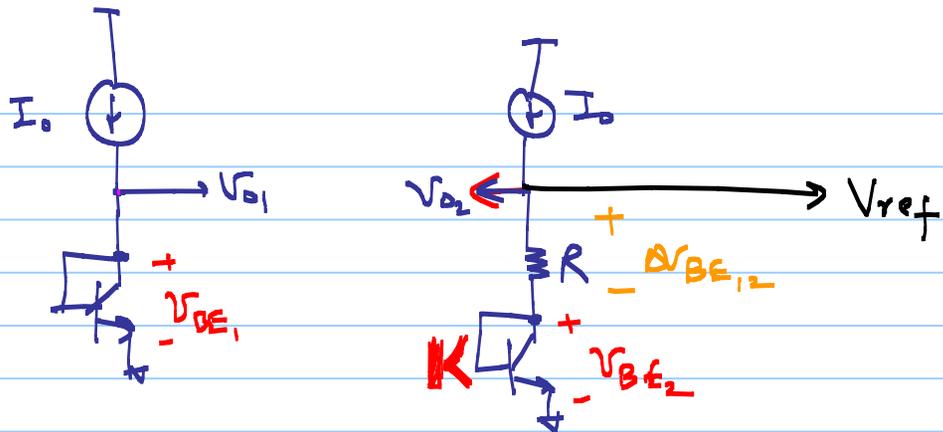
\Rightarrow

$$V_{REF} = V_{BE} + 17.2 V_T$$

$$\approx 0.75 + 17.2 \times 26 \text{ mV}$$

$$= 1.2 \text{ V}$$

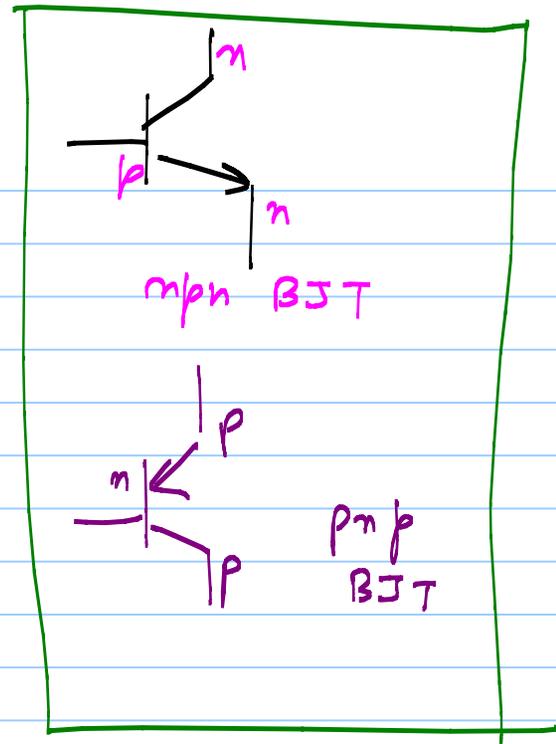




If we somehow force $V_{D1} = V_{D2}$

$$V_{BE1} = V_{BE2} + I_0 R$$

$$I_0 R = V_{BE1} - V_{BE2} = \underline{V_T \ln k} \longrightarrow \textcircled{1}$$



$$V_{G2} = V_{BE2} + I_0 R$$

↓

$$V_{REF} = \underbrace{V_{BE2}}_{CTAT} + \underbrace{V_T \ln k}_{PTAT}$$

we can find a value

for k s.t.

$$\frac{\partial V_{REF}}{\partial T} = 0$$

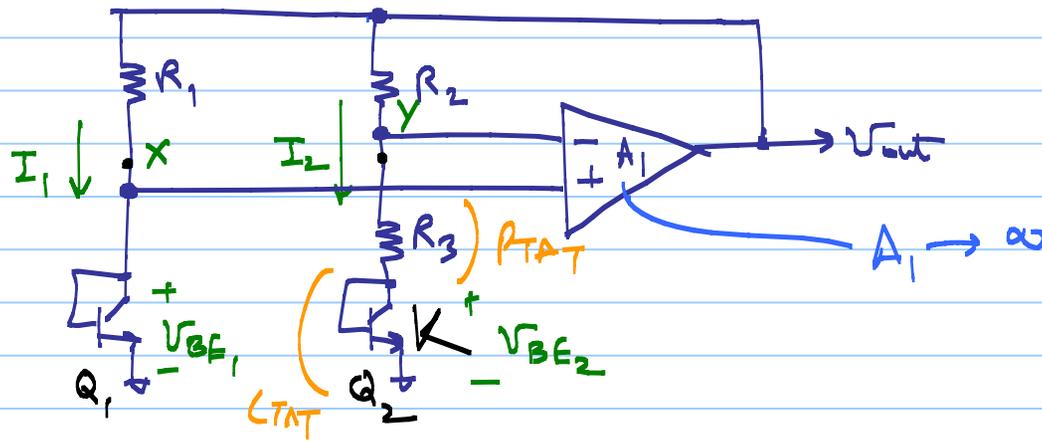
Here, $\alpha_1 = \alpha_2 = 1$

$$\alpha_2 \ln k = 17.2$$

$$\Rightarrow k = e^{17.2} \leftarrow \text{Impractical}$$

Need to introduce $\alpha_2 > 1$

"Need a Suitable
Start-up Circuit"



Let $R_1 = R_2$, force $V_x = V_y$ using feedback

$$V_{BE1} - V_{BE2} = V_T \ln k$$

$$\Rightarrow \boxed{I_2 = \frac{V_T \ln k}{R_3}}$$

$$V_{out} = V_{BE2} + I_2 \cdot (R_2 + R_3)$$

$$= V_{BE2} + \frac{V_T \ln k}{R_3} (R_2 + R_3)$$

$$= \underbrace{V_{BE2}}_{CTAT} + \underbrace{\left(1 + \frac{R_2}{R_3}\right)}_{\alpha_2} \underbrace{V_T \ln k}_{PTAT}$$

$$\alpha_1 = 1$$

$$\alpha_2 = 1 + \frac{R_2}{R_3}$$

For $TC = 0$,

$$\left(1 + \frac{R_2}{R_3}\right) \ln k = 17.2$$

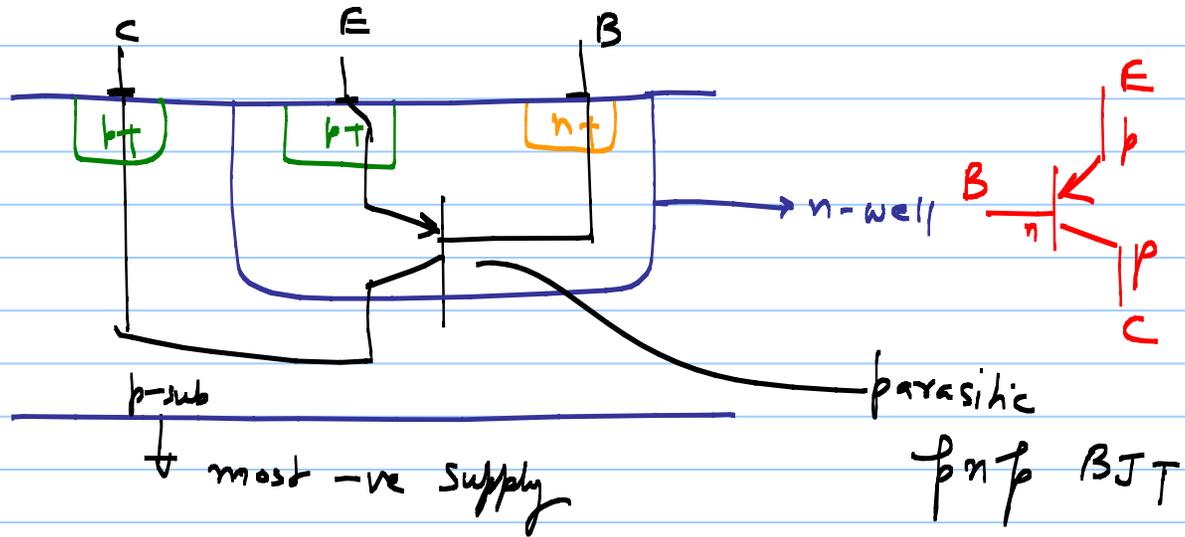
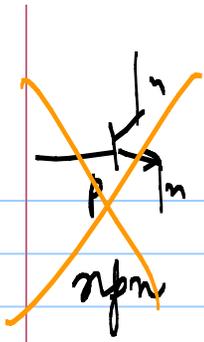
Several solutions (R_2, R_3, k)

Example:

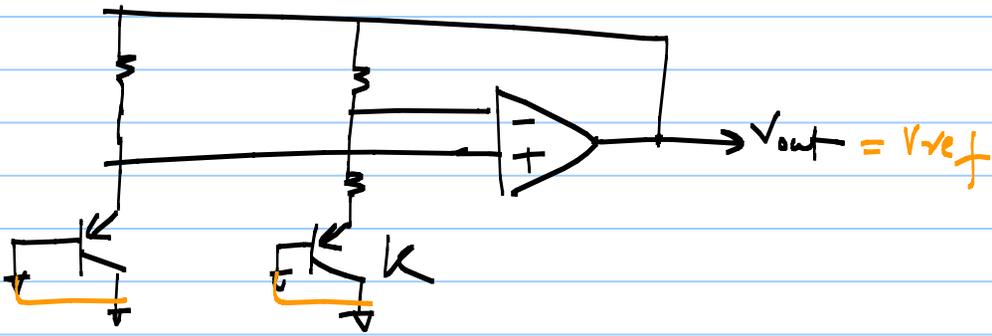
$$k = 31, \quad \frac{R_2}{R_3} = 4$$

.....



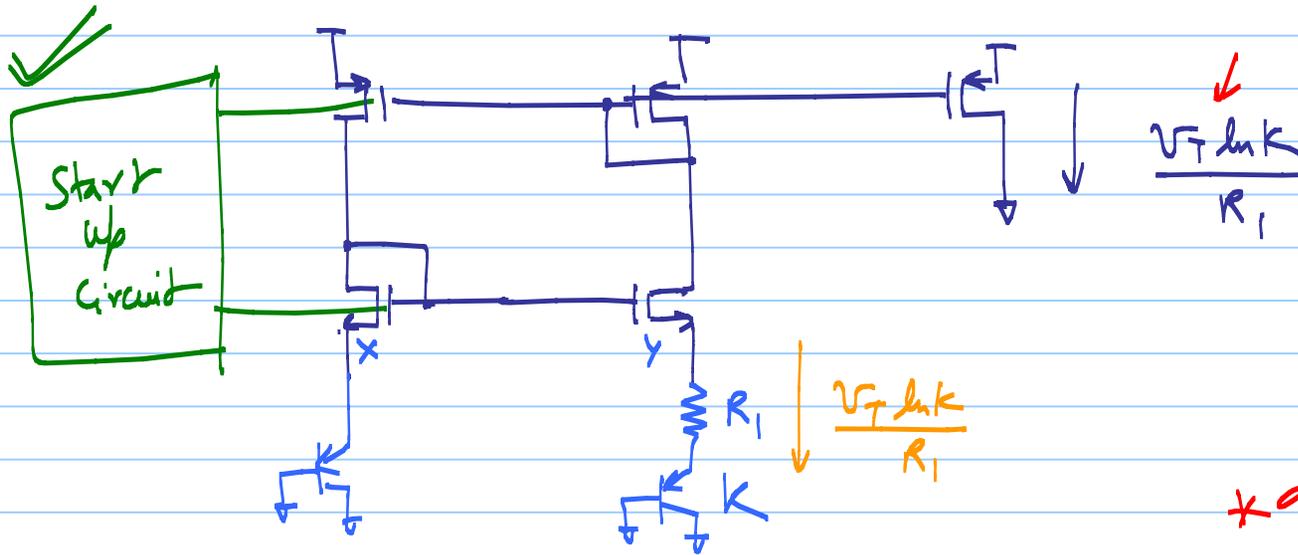


Redraw the BJT for CMOS implementation



"Start-up Circuit"

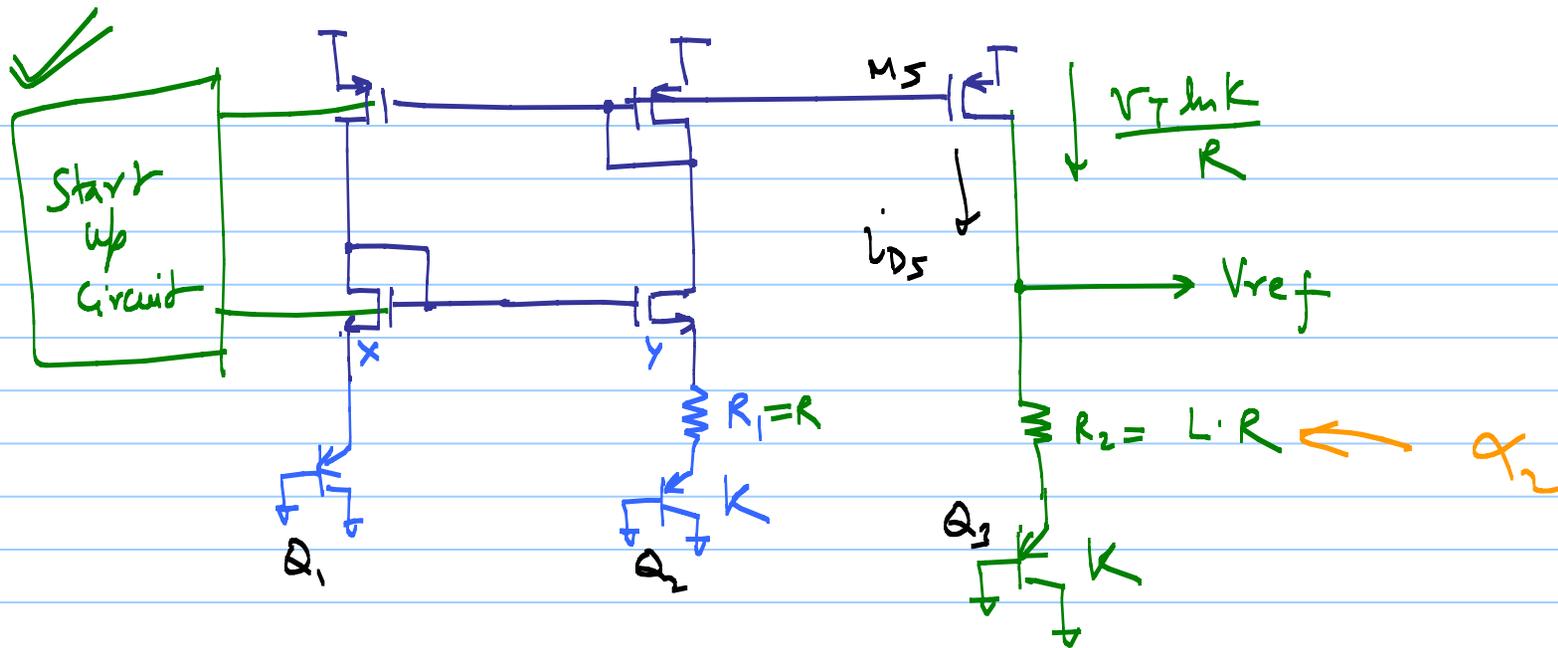
BMK - type BGR Circuit



$$\frac{V_T \ln K}{R_1}$$

$\frac{PTAT}{R}$ Current

x all R's have same Temp Co



$$V_{ref} = i_{D5} \cdot R_2 + V_{BE3}$$

$$= \frac{V_T \ln K}{R_1} \cdot R_2 + V_{BE3}$$

$$= \underbrace{V_{BE3}}_{CTAT} + \frac{L}{\alpha_2} \underbrace{V_T \ln(K)}_{PTAT}$$

Ex. $I_D = 1 \mu A$

Select $K=8$,

$$L = \frac{\left| \left(\frac{\partial V_{BE}}{\partial T} \right) \right|}{\ln(K) \left(\frac{1}{2} \right)} = \frac{1.5}{0.085 \times \ln(8)} = 8.4834$$

$$V_{ref} = V_{BE3} + L \cdot V_T \ln K \approx 1.25V$$

* Can use cascoding or drain regulated BMR
for improved ^{current} matching in nano-CMOS

$$V_{ref} = (I_{PTAT} + I_{CTAT}) \cdot N \cdot R$$

$$= \left(\frac{V_T \ln k}{R} + \frac{V_{BE1}}{L \cdot R} \right) \cdot N \cdot R$$

$$\Rightarrow V_{ref} = \underbrace{N}_{\alpha_2} \cdot \underbrace{V_T \ln(k)}_{PTAT} + \underbrace{\left(\frac{N}{L}\right)}_{\alpha_1} \cdot \underbrace{V_{BE1}}_{CTAT}$$

$$\alpha_2 > 1$$

$$\alpha_1 < 1$$

$$V_{ref} < 1V$$

$$V_{ref} = N \cdot (V_T \ln k) + \left(\frac{N}{L}\right) V_{BE1}$$

$$\frac{\partial V_{ref}}{\partial T} \Rightarrow \Rightarrow \cancel{N \cdot \ln(k) \left(\frac{k}{L}\right)} + \cancel{\frac{N}{L}} \cdot \left(\frac{\partial V_{BE1}}{\partial T}\right) = 0$$

$$\Rightarrow L = \frac{1.5 \text{ mV}/\mu}{\ln(k) \times 0.095 \text{ mV}/\mu}$$

$$\text{Choose } \boxed{k=8} \Rightarrow \boxed{L=9.41}$$



$$\times \quad V_{ref} = V_T \ln(k) N + \frac{N}{L} V_{BE1}$$

$$\Rightarrow N = \frac{V_{ref}}{V_T \ln(k) + V_{BE1}/L}$$

$$f_v \quad V_{REF} = 0.5V$$

$$\Rightarrow N = \frac{0.5}{0.052 + \frac{0.7}{9.41}} = \boxed{3.71}$$

* Why its called "Band gap" Reference

$$V_{ref} = V_{BE} + V_T \ln(k)$$

Also $\frac{\partial V_{ref}}{\partial T} = 0 \Rightarrow \frac{\partial V_{BE}}{\partial T} + \frac{V_T}{T} \ln(k) = 0$

$$\Rightarrow \frac{V_{BE} - (4+m)V_T - E_g/2}{T} = -\frac{V_T}{T} \ln(k)$$

↓ gives a value for V_{BE}

$$\Rightarrow V_{ref} = V_{BE} - V_{BE} + (4+m)V_T + E_g/2$$

$$\Rightarrow V_{ref} = \frac{E_g}{q} + (4+m)V_T$$

ZTC voltage is given by two fundamental numbers
↳ Bandgap Energy of Si
↳ m & V_T

$$T \rightarrow 0K \Rightarrow V_{ref} \rightarrow \frac{E_g}{q} \approx 1.12V$$

